2SD1259, 2SD1259A

Silicon NPN triple diffusion planar type

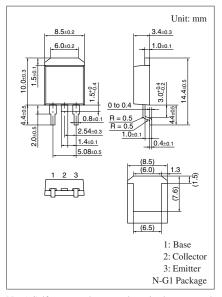
For power amplification with high forward current transfer ratio

■ Features

- High forward current transfer ratio h_{FE}
- \bullet Satisfactory linearity of forward current transfer ratio $h_{\mbox{\scriptsize FE}}$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SD1259	V _{CBO}	80	V
(Emitter open)	2SD1259A		100	
Collector-emitter voltage	2SD1259	V _{CEO}	60	V
(Base open)	2SD1259A		80	
Emitter-base voltage (Col	V _{EBO}	6	V	
Collector current	I_C	3	A	
Peak collector current	I_{CP}	6	A	
Base current	I_{B}	1	A	
Collector power dissipation		P _C	40	W
	$T_a = 25$ °C		1.3	
Junction temperature		T_{j}	150	°C
Storage temperature		T _{stg}	-55 to +150	°C



Note) Self-supported type package is also prepared.

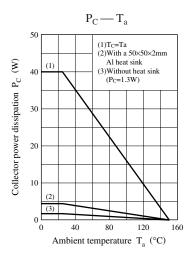
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

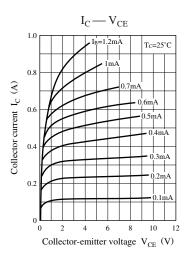
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SD1259	V _{CEO}	$I_C = 25 \text{ mA}, I_B = 0$	60			V
(Base open)	2SD1259A			80			
Collector-emitter cutoff	2SD1259	I_{CBO}	$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	μΑ
current (Emitter open)	2SD1259A		$V_{CB} = 100 \text{ V}, I_E = 0$			100	
Collector-emitter cutoff current (Base open)		I_{CEO}	$V_{CE} = 40 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)		I_{EBO}	$V_{EB} = 6 \text{ V,I}_{C} = 0$			100	μΑ
Forward current transfer ratio		h _{FE} *	$V_{CE} = 4 \text{ V}, I_{C} = 0.5 \text{ A}$	500		2500	_
Collector-emitter saturation voltage		V _{CE(sat)}	$I_C = 2 A, I_B = 0.05 A$			1.0	V
Transition frequency		f_T	$V_{CE} = 12 \text{ V}, I_{C} = 0.2 \text{ A}, f = 10 \text{ MHz}$		50		MHz

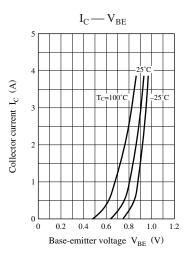
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

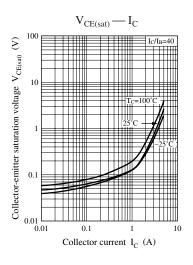
2. *: Rank classification

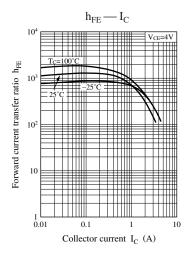
Rank	Q	Р	0	
h_{FE}	500 to 1 000	800 to 1500	1200 to 2500	

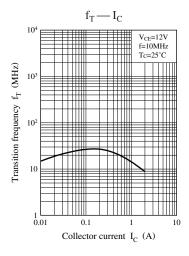


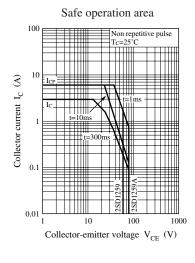


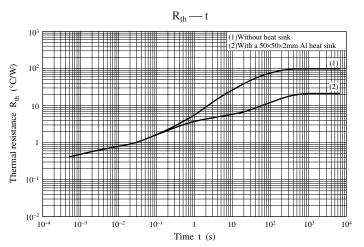












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